

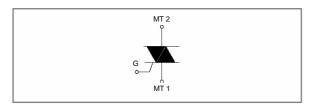
# 0.8A TRIACS

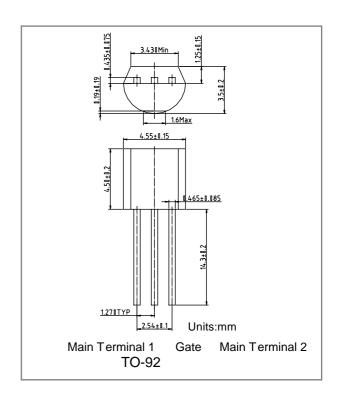
## **MAIN FEATURES:**

Symbol V	alue	Unit
I <sub>T(RMS)</sub>	0.8	Α
$V_{DRM}/V_{RRM}$	600	V
I <sub>GT(Q1)</sub>	5	mA

#### **DESCRIPTION**

The Z0607 is suitable for low power AC switching applications, such as fan speed, small light controllers... Thanks to low gate triggering current, it can be directly driven by microcontrollers.





### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter			Value Unit	
I <sub>T(RMS)</sub>	RMS on-state current (full sine wave)		TI=50 0.8		Α
I <sub>TSM</sub>	Non repetitive surge peak on -state	F=50Hz t=20r	ns	9	Α
	current (full cycle, Tj initial=25 )	F=60Hz t=16.	7ms	9.5	А
l²t l	<sup>2</sup> t Value for fusing	tp=1	0ms	0.45	$A^2s$
dI/dt	Critical rate of rise of on-state current	F=120Hz Tj=1	10 20		A/μs
	I <sub>G</sub> =2*I <sub>GT</sub> , tr 100ns				
$I_{GM}$	Peak gate current	tp=20 μ s T	j=110 1		Α
P <sub>G(AV</sub> )	Average gate power dissipation		Tj=110 0.1		W
T <sub>stg</sub>	Storage junction temperature range		-40 to +150		
Tj	Operating junction temperature range		-40 to +110		



## **ELECTRICAL CHARACTERISTICS** (Tj = 25°C, unless otherwise specified)

Symbol	Test condition	Quadrant		Value	Unit
I <sub>GT</sub> (1)			MAX. 5		mA
	$V_D=12V R_L=30$	IV		7	
$V_{GT}$		ALL MAX		1.3	V
$V_{\sf GD}$	$V_D=V_{DRM}$ $R_L=3.3K$ $Tj=110$ ALL		MIN.	0.2	V
I <sub>H</sub> (2) I	<sub>T</sub> =200mA MAX.			5	mA
IL	I <sub>G</sub> =1.2I <sub>GT</sub>		MAX.	10	mA
				20	
dV/dt(2) V	<sub>D</sub> =67%V <sub>DRM</sub> gate open Tj=110 MIN.			10	V/µs
(dV/dt)c(2)	(dV/dt)c=0.35A/ms Tj =110 MIN.			1.5	V/µs

### STATIC CHARACTERISTICS

Symbol	Test condition			Value	Unit
V <sub>TM</sub> (2) I	<sub>TM</sub> =1.1A tp= 380 µ s T	j=25 MAX	•	1.5	V
V <sub>to</sub> (2) Thresh	old voltage	Tj=110 MAX	<b>K</b> .	0.95	V
R <sub>d</sub> (2) D	ynamic resistance	Tj=110 MAX	<b>K</b> .	420	m
I <sub>DRM</sub>	$V_{DRM} = V_{RRM} = 600V$	Tj=25 5	MAX.		μА
I <sub>RRM</sub>		Tj=110		0.1 mA	

Note 1: minimum IGT is guaranted at 5% of IGT max.

Note 2: for both polarities of Main Terminal 2 referenced to Main Terminal 1

## THERMAL RESISTANCES

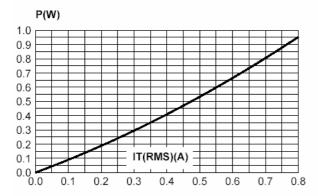
Symbol	Parameter V	alue	Unit
R <sub>th(j-l)</sub>	Junction to lead (AC)	60	/W
R <sub>th(j-a)</sub>	Junction to ambient	150	/W

### **PRODUCT SELECTOR**

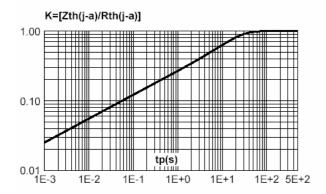
Part Number	Voltage Sensit	i vity	Туре	Package
Z0607	600V	5mA	Standard	TO-92



Fig. 1: Maximum power dissipation versus RMS on-state current (full cycle).



**Fig. 3:** Relative variation of thermal impedance junction to ambient versus pulse duration.



**Fig. 5:** Surge peak on-state current versus number of cycles.

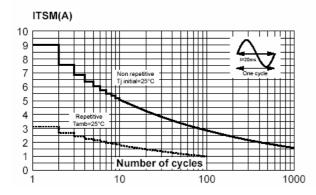
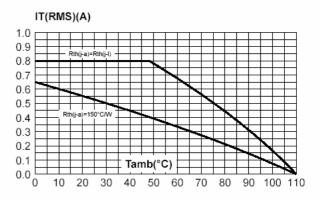
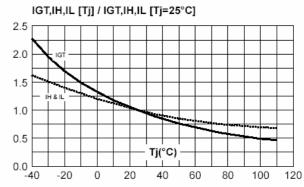


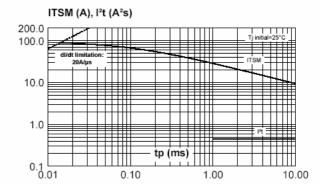
Fig. 2: RMS on-state current versus ambient temperature (full cycle).



**Fig. 4:** Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values).

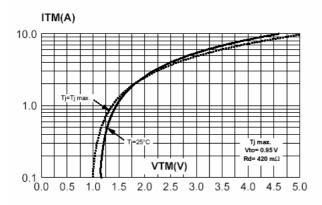


**Fig. 6:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp < 10ms, and corresponding value of  $I^2t$ .





**Fig. 7:** On-state characteristics (maximum values).



**Fig. 9:** Relative variation of critical rate of decrease of main current versus junction temperature.

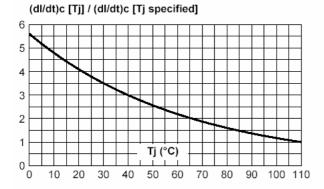


Fig. 8: Relative variation of critical rate of decrease of main current versus (dV/dt)c (typical values).

